

## SPECIFICATION OF INFRARED LED CHIP

CN850-35P

[INFRARED]

### 1) Commodity Type and Physical Characteristics.

- |                      |                    |                   |            |
|----------------------|--------------------|-------------------|------------|
| 1. Material          | GaAlAs/GaAlAs(DDH) |                   |            |
| 2. Electrode         | Top Side           | P ( anode )side   | : Au Alloy |
|                      | Bottom Side        | N ( cathode )side | : Au Alloy |
| 3. Electrode Pattern | Fig.1              |                   |            |
| 4. Chip Size         | Fig.2              |                   |            |
| 5. Chip Thickness    | Fig.2              |                   |            |
| 6. Emission Area     | Fig.2              |                   |            |

### 2) Electro-Optical Characteristics

| parameters                   | symbol         | condition            | min. | typ. | max. | unit |
|------------------------------|----------------|----------------------|------|------|------|------|
| Forward Voltage              | V <sub>f</sub> | I <sub>f</sub> =20mA |      | 1.4  | 1.6  | V    |
| Reverse Current              | I <sub>r</sub> | V <sub>r</sub> =5V   |      |      | 10   | uA   |
| Power Intensity              | P <sub>o</sub> | I <sub>f</sub> =20mA | 3.0  | 5.0  |      | mW   |
| Peak Wavelength              | λ <sub>p</sub> | I <sub>f</sub> =20mA | 840  | 850  | 860  | nm   |
| Spectral Radiation Bandwidth | Δλ             | I <sub>f</sub> =20mA |      | 35   |      | nm   |
| RiseTime                     | t <sub>r</sub> | I <sub>f</sub> =20mA |      | 30   |      | ns   |
| FallTime                     | t <sub>f</sub> | I <sub>f</sub> =20mA |      | 25   |      | ns   |

‡Die shall be mounted on TO-18 gold header without resin coated.(T<sub>a</sub>=25°C)

[Unit : um]

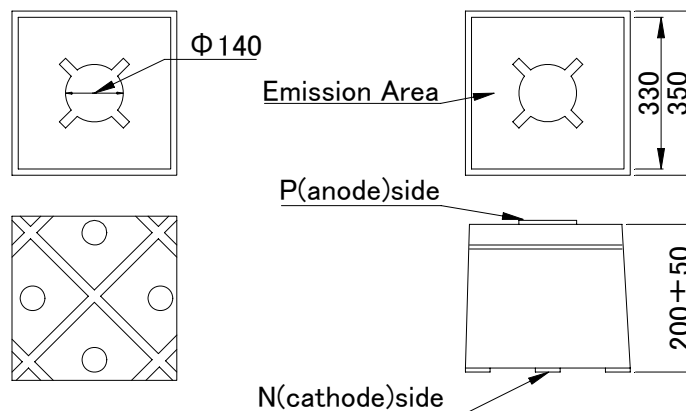


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area